In the Claims:

The following replacement claims are respectfully submitted:

21. (Twice Amended) A method for fabricating a semiconductor apparatus, comprising:

fabricating a semiconductor substrate having a first surface in which a semiconductor integrated circuit is formed,

the semiconductor substrate including a conductive layer formed on the first surface thereof which is connected to the semiconductor integrated circuit and including a base member of insulating material arranged between the first surface and the conductive layer,

the base member including a first surface facing the first surface of the semiconductor substrate and a second surface opposite the first surface of the base member,

the conductive layer having an extended portion extending on the second surface of the base member;

providing a connection substrate on which the semiconductor substrate is to be mounted;

placing the semiconductor substrate so that the first surface of the semiconductor substrate faces the connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

supplying a seal member in a space between the semiconductor substrate and the connection substrate.

22. (Amended) A method according to claim 21, wherein the first surface of the semiconductor substrate is placed to face the connection substrate using a face down technique.

23. (Amended) A method according to claim 21, wherein the base member and the seal member are made of a same material having a same thermal expansion coefficient.

Please add claims 24-27 as follows:

--24. A method according to claim 21, wherein the conductive layer and the base member constitute an electrode.

25. A method for fabricating a semiconductor apparatus comprising:

forming a semiconductor integrated circuit on a first surface of a semiconductor substrate;

forming a base member of insulating material on the first surface of the semiconductor substrate;

forming a conductive layer on the first surface of the semiconductor substrate, the conductive layer being connected to the semiconductor integrated circuit and having an extended portion that extends onto a top surface of the base member;

placing the first surface of the semiconductor substrate having the semiconductor integrated circuit, the base member and the conductive layer thereon as facing a connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

supplying a sealing member in a space between the semiconductor substrate and the connection substrate, after said connecting.

26. A method according to claim 25, wherein the base member and the sealing member are a same material.

27. A method according to claim 26, wherein the base member and the sealing member have a same thermal expansion coefficient.--